

2SB956

Silicon PNP epitaxial planer type

For low-frequency power amplification

Complementary to 2SD1280

Features

- Large collector power dissipation P_C .
- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-20	V
Collector to emitter voltage	V_{CEO}	-20	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-2	A
Collector current	I_C	-1	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

* Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7mm for the collector portion

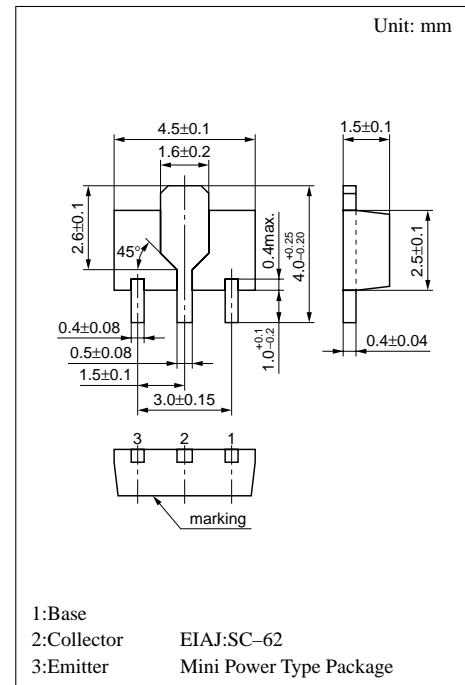
Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -10\text{V}, I_E = 0$			-1	μA
Collector to emitter voltage	V_{CEO}	$I_C = -1\text{mA}, I_B = 0$	-20			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = -2\text{V}, I_C = -500\text{mA}^{*2}$	130		280	
	h_{FE2}	$V_{CE} = -2\text{V}, I_C = -1.5\text{A}^{*2}$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}, I_B = -50\text{mA}^{*2}$			-0.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CB} = -6\text{V}, I_E = 50\text{mA}, f = 200\text{MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{V}, I_E = 0, f = 1\text{MHz}$		40		pF

*2 Pulse measurement

*1 h_{FE1} Rank classification

Rank	R	S
h_{FE1}	130 ~ 210	180 ~ 280
Marking Symbol	HR	HS



Marking symbol : H

